

Doyeol Ahn

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

179
papers

3,132
citations

27
h-index

50
g-index

189
ext. papers

3,400
ext. citations

2.4
avg, IF

5.24
L-index

| # | Paper | IF | Citations |
|-----|--|-----|-----------|
| 179 | Experimental realization of Schumacher's information geometric Bell inequality. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2021 , 405, 127444 | 2.3 | 6 |
| 178 | Intrinsically p-type cuprous iodide semiconductor for hybrid light-emitting diodes. <i>Scientific Reports</i> , 2020 , 10, 3995 | 4.9 | 12 |
| 177 | Strain relaxation effects on TE-polarized light emission and in-plane polarization ratio in c-plane ultraviolet AlGaIn/AlN quantum well structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2020 , 120, 114112 | 3 | |
| 176 | Effect of Coupled Quantum-Dot Insertion on the Radiative Recombination Probability of Wurtzite InGaIn/GaN Quantum Dots. <i>Journal of the Korean Physical Society</i> , 2020 , 76, 55-58 | 0.6 | |
| 175 | Speedup of Grover's search algorithm and closed timelike curves. <i>Quantum Science and Technology</i> , 2020 , 5, 045011 | 5.5 | 0 |
| 174 | Temperature-Dependent Polarized Photoluminescence from c-plane InGaIn/GaN Multiple Quantum Wells Grown on Stripe-Shaped Cavity-Engineered Sapphire Substrate. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900526 | 1.3 | 1 |
| 173 | Effects of GaN capping layer on carrier occupation and interband transition probability of vertically coupled InGaIn/GaN quantum dots. <i>Physica B: Condensed Matter</i> , 2020 , 578, 411846 | 2.8 | |
| 172 | Quantum circuit optimization using quantum Karnaugh map. <i>Scientific Reports</i> , 2020 , 10, 15651 | 4.9 | 6 |
| 171 | Non-Polar Wurtzite (1120) GaN/AlN Quantum Dots for Highly Efficient Opto-Electronic Devices. <i>Electronics (Switzerland)</i> , 2020 , 9, 1256 | 2.6 | 0 |
| 170 | Theoretical study of optical properties of non-polar AlGaIn/AlN quantum wells lattice-matched to AlN. <i>Solid State Communications</i> , 2019 , 290, 67-69 | 1.6 | 2 |
| 169 | Strain and built-in potential effects on optical properties of wurtzite GaN/AlInN quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2019 , 108, 112-115 | 3 | 0 |
| 168 | Lattice-matched double dip-shaped AlGaIn/AlN quantum well structures for ultraviolet light emission devices. <i>Superlattices and Microstructures</i> , 2018 , 117, 413-417 | 2.8 | 3 |
| 167 | Hawking effects as a noisy quantum channel. <i>Journal of the Korean Physical Society</i> , 2018 , 72, 201-207 | 0.6 | |
| 166 | A model for the InGaAs/InP single photon avalanche diodes with multiple-quantum wells in the charge multiplication region. <i>Journal of the Korean Physical Society</i> , 2018 , 72, 289-293 | 0.6 | 0 |
| 165 | Substrate dependence of TM-polarized light emission characteristics of AlGaIn/AlN quantum wells. <i>Optics Communications</i> , 2018 , 417, 76-78 | 2 | 1 |
| 164 | Unruh effect as a noisy quantum channel. <i>Physical Review A</i> , 2018 , 98, | 2.6 | 3 |
| 163 | P-type wurtzite GaN/AlGaIn quantum well structures for normal incidence inter-subband photodetectors at 1.55 μm . <i>Applied Physics Express</i> , 2018 , 11, 114001 | 2.4 | |

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|-----|---|-----|----|
| 162 | Dip-Shaped AlGa _N /AlN Light-Emitting Diodes With Delta-Layer Containing Boron. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1042-1045 | 2.2 | 2 |
| 161 | Effects of a delta-layer insertion on the ultraviolet light emission characteristics of III-nitride quantum well structures. <i>Superlattices and Microstructures</i> , 2017 , 112, 665-670 | 2.8 | 3 |
| 160 | Intersubband absorption of p-type wurtzite GaN/AlN quantum well for fiber-optics telecommunication. <i>Journal of Applied Physics</i> , 2017 , 122, 184303 | 2.5 | 2 |
| 159 | Intersubband transition in lattice-matched B _{0.2} Ga _{0.8} N/AlN quantum well structures with high absorption coefficients. <i>Optics Express</i> , 2017 , 25, 3143-3152 | 3.3 | 9 |
| 158 | Theoretical Studies on TM-Polarized Light Emission for Ultraviolet BAlGa _N /AlN Optoelectronic Devices. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 2153-2155 | 2.2 | 6 |
| 157 | Cuprous halides semiconductors as a new means for highly efficient light-emitting diodes. <i>Scientific Reports</i> , 2016 , 6, 20718 | 4.9 | 30 |
| 156 | Effect of boron incorporation on light emission characteristics of UV BAlGa _N /AlN quantum well structures. <i>Applied Physics Express</i> , 2016 , 9, 021001 | 2.4 | 3 |
| 155 | Theoretical studies on light emission characteristics of high-efficiency BInGa _N /Ga _N quantum well structures with blue spectral range. <i>Superlattices and Microstructures</i> , 2016 , 96, 150-154 | 2.8 | 2 |
| 154 | Reply to Comment on 'Magnetic bead detection using nano-transformers'. <i>Nanotechnology</i> , 2016 , 27, 418002 | 3.4 | |
| 153 | Intersubband absorption coefficients of Ga _N /Al _N and strain-compensated InGa _N /InAl _N quantum well structures. <i>Superlattices and Microstructures</i> , 2016 , 100, 508-513 | 2.8 | 3 |
| 152 | Investigation of humidity-dependent size control of local anodic oxidation on graphene by using atomic force microscopy. <i>Journal of the Korean Physical Society</i> , 2015 , 66, 617-620 | 0.6 | 2 |
| 151 | Optical Gain Characteristics in GaAsPN/GaPN Quantum Well Lasers for Silicon Integration. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2015 , 21, 153-159 | 3.8 | 2 |
| 150 | Full wave finite-difference time-domain study of lossless acoustic bipolar cylindrical cloak with compressed geometry and complementary media. <i>Journal of Applied Physics</i> , 2015 , 118, 044508 | 2.5 | 2 |
| 149 | Theoretical study of a two-dimensional electron gas in wurtzite ZnO/MgZnO heterostructures and comparison with experiment. <i>Journal of the Korean Physical Society</i> , 2015 , 67, 1844-1847 | 0.6 | 1 |
| 148 | FDTD Study of Half Cloak in Bipolar Cylindrical Shape With Compressed Geometry and Complementary Media. <i>IEEE Transactions on Antennas and Propagation</i> , 2015 , 63, 2317-2320 | 4.9 | 2 |
| 147 | Optical polarization characteristics of m-plane Ga _N /AlGa _N quantum well structures grown on m-plane SiC substrate. <i>Solid State Communications</i> , 2015 , 223, 16-18 | 1.6 | |
| 146 | Effects of wetting layer on exciton binding energy of strained CdTe/ZnTe pyramidal quantum dots. <i>Solid State Communications</i> , 2015 , 204, 61-63 | 1.6 | 3 |
| 145 | Internal field effects on electronic and optical properties of ZnO/BeZnO quantum well structures. <i>Physica B: Condensed Matter</i> , 2014 , 441, 12-16 | 2.8 | 9 |

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|-----|--|-----|----|
| 144 | Elliptic cylindrical pseudo-optical black hole for omnidirectional light absorber. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2014 , 31, 1948 | 1.7 | 4 |
| 143 | Optical Emission Characteristics of Pseudopolarization-Matched Green AlInGaN/InGaN Quantum Well Structures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 1-8 | 3.8 | 4 |
| 142 | Optical polarization characteristics of m-plane InGaN/GaN quantum well structures and comparison with experiment. <i>Applied Physics Letters</i> , 2013 , 103, 101107 | 3.4 | 2 |
| 141 | High optical gain of III-V semiconductor quantum wells for efficient light-emitting devices. <i>Applied Physics Letters</i> , 2013 , 102, 121114 | 3.4 | 11 |
| 140 | Crystal orientation effect on intersubband transition properties of (11 \bar{n})-oriented ZnCdTe/ZnTe semiconductor quantum dots. <i>Physica B: Condensed Matter</i> , 2013 , 420, 36-39 | 2.8 | |
| 139 | Electronic structure of p(2 \times 2) Ag films on Si(100). <i>Journal of the Korean Physical Society</i> , 2013 , 62, 86-91 | 0.6 | 3 |
| 138 | Quantum-state cloning in the presence of a closed timelike curve. <i>Physical Review A</i> , 2013 , 88, | 2.6 | 19 |
| 137 | Full-wave finite-difference time-domain analysis of the invisibility cloak mapped to a line segment with isotropic complementary media. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013 , 30, 2148 | 1.7 | 4 |
| 136 | Dispersive full-wave finite-difference time-domain analysis of the bipolar cylindrical cloak based on the effective medium approach. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013 , 30, 140 | 1.7 | 6 |
| 135 | Hybrid InGaN/CdZnO quantum well structures for optoelectronic applications in the short wavelength spectral region. <i>Physica Status Solidi (B): Basic Research</i> , 2013 , 250, 378-381 | 1.3 | 3 |
| 134 | Dispersive finite-difference time-domain (FDTD) analysis of the elliptic cylindrical cloak. <i>Journal of the Korean Physical Society</i> , 2012 , 60, 1349-1360 | 0.6 | 3 |
| 133 | Black hole state evolution, final state and Hawking radiation. <i>Classical and Quantum Gravity</i> , 2012 , 29, 224007 | 3.3 | 2 |
| 132 | Spontaneous emission and optical gain characteristics of blue InGaAlN/InGaN quantum well structures with reduced internal field. <i>Journal of Applied Physics</i> , 2012 , 112, 043107 | 2.5 | 6 |
| 131 | Comparison of light emission in InGaN/GaN light-emitting diodes with graded, triangular, and parabolic quantum-well structures. <i>Journal of the Korean Physical Society</i> , 2012 , 60, 505-508 | 0.6 | 8 |
| 130 | High optical polarization ratio of semipolar (202 $\bar{1}0$)-oriented InGaN/GaN quantum wells and comparison with experiment. <i>Journal of Applied Physics</i> , 2012 , 112, 093106 | 2.5 | 5 |
| 129 | High-efficiency InGaN/GaN light-emitting diodes with electron injector. <i>Semiconductor Science and Technology</i> , 2012 , 27, 115003 | 1.8 | 6 |
| 128 | Effect of indirect interband absorption in Ge/SiGe quantum wells. <i>Journal of Applied Physics</i> , 2011 , 110, 083119 | 2.5 | 8 |
| 127 | . <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 2520-2524 | 2.9 | 12 |

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|-----|--|-----|----|
| 126 | Spontaneous emission rate of green strain-compensated InGaN/InGaN LEDs using InGaN substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 195-198 | 1.6 | 33 |
| 125 | Light emission enhancement in blue InGaAlN/InGaN quantum well structures. <i>Applied Physics Letters</i> , 2011 , 99, 181101 | 3.4 | 31 |
| 124 | Calculation of permittivity tensors for invisibility devices by effective medium approach in general relativity. <i>Journal of Modern Optics</i> , 2011 , 58, 700-710 | 1.1 | 7 |
| 123 | 2011 , | | 16 |
| 122 | Enhancement of light power for strain-compensated hybrid InGaN/InGaN/MgZnO light-emitting diodes. <i>Applied Physics Letters</i> , 2010 , 97, 121107 | 3.4 | 2 |
| 121 | Optical gain improvement in type-II InGaN/GaN/Sb/GaN quantum well structures composed of InGaN/and GaN/Sb layers. <i>Applied Physics Letters</i> , 2010 , 96, 051106 | 3.4 | 27 |
| 120 | Magnetic bead detection using nano-transformers. <i>Nanotechnology</i> , 2010 , 21, 465501 | 3.4 | 2 |
| 119 | Temperature Dependent Study of Random Telegraph Noise in Gate-All-Around PMOS Silicon Nanowire Field-Effect Transistors. <i>IEEE Nanotechnology Magazine</i> , 2010 , 9, 754-758 | 2.6 | 13 |
| 118 | Explicit continuous current-voltage (I-V) models for fully-depleted surrounding-gate MOSFETs (SGMOSFETs) with a finite doping body. <i>Journal of Nanoscience and Nanotechnology</i> , 2010 , 10, 3316-20 | 1.3 | 1 |
| 117 | Analytical Threshold Voltage Model Including Effective Conducting Path Effect (ECPE) for Surrounding-Gate MOSFETs (SGMOSFETs) With Localized Charges. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 3176-3180 | 2.9 | 25 |
| 116 | Enhancement of optical gain in Li: CdZnO/ZnMgO quantum well lasers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 2652-2654 | 3 | 2 |
| 115 | Electronic and optical properties of staggered InGaN/InGaN quantum-well light-emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 2637-2640 | 1.6 | 20 |
| 114 | Electrical transport properties of a single wall carbon nanotube network. <i>Physica Status Solidi (B): Basic Research</i> , 2009 , 246, 744-746 | 1.3 | 4 |
| 113 | A SPICE-Compatible New Silicon Nanowire Field-Effect Transistors (SNWFETs) Model. <i>IEEE Nanotechnology Magazine</i> , 2009 , 8, 643-649 | 2.6 | 14 |
| 112 | High-efficiency staggered 530 nm InGaN/InGaN/GaN quantum-well light-emitting diodes. <i>Applied Physics Letters</i> , 2009 , 94, 041109 | 3.4 | 77 |
| 111 | Dip-shaped InGaN/GaN quantum-well light-emitting diodes with high efficiency. <i>Applied Physics Letters</i> , 2009 , 95, 063507 | 3.4 | 61 |
| 110 | Internal field engineering in CdZnO/MgZnO quantum well structures. <i>Applied Physics Letters</i> , 2009 , 94, 083507 | 3.4 | 12 |
| 109 | Transport Properties of a DNA-Conjugated Single-Wall Carbon Nanotube Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 06FD08 | 1.4 | 6 |

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| 108 | A Bottom-gate Depletion-mode Nanowire Field Effect Transistor(NWFET) Model Including a Schottky Diode Model. <i>Journal of the Korean Physical Society</i> , 2009 , 55, 1162-1166 | 0.6 | 2 |
| 107 | Optical gain in InGaN/GaN quantum well structures with zero internal field. <i>Applied Physics Letters</i> , 2008 , 92, 171115 | 3.4 | 21 |
| 106 | Fabrication of one-dimensional devices by a combination of AC dielectrophoresis and electrochemical deposition. <i>Nanotechnology</i> , 2008 , 19, 105305 | 3.4 | 14 |
| 105 | Microwave Characterization of a Single Wall Carbon Nanotube Bundle. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 4965-4968 | 1.4 | 11 |
| 104 | Faraday's Induction Experiment in Nano-Transformers. <i>IEEE Nanotechnology Magazine</i> , 2008 , 7, 120-123 | 2.6 | 4 |
| 103 | Electronic transport properties of a single-wall carbon nanotube field effect transistor with deoxyribonucleic acid conjugation. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 1115-1117 | 3 | 8 |
| 102 | Impurity scattering effects on transport through gate-all-around Si nanowires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 1526-1529 | 3 | |
| 101 | Hybrid integration of GaAs/AlGaAs in-plane-gate resonant tunneling and field effect transistors. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 2160-2162 | 3 | 3 |
| 100 | Effects of Confinement on the Valley Splitting of Si Quantum Structures. <i>Journal of the Korean Physical Society</i> , 2008 , 53, 3322-3327 | 0.6 | 2 |
| 99 | Electronic and Optical Properties of 1.55 μm GaInNAs/GaAs Quantum-Well Structures. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 152-155 | 1.4 | |
| 98 | Hawking-Unruh effect and the entanglement of two-mode squeezed states in Riemannian spacetime. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2007 , 366, 202-205 | 2.3 | 17 |
| 97 | Transmission-Type Radio-Frequency Single-Electron Transistor with In-Plane-Gate Single-Electron Transistor. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 2592-2595 | 1.4 | 2 |
| 96 | Electronic and Optical Properties of a - and m -Plane Wurtzite InGaNGaN Quantum Wells. <i>IEEE Journal of Quantum Electronics</i> , 2007 , 43, 1175-1182 | 2 | 103 |
| 95 | Observation of three-dimensional shell filling in cylindrical silicon nanowire single electron transistors. <i>Applied Physics Letters</i> , 2007 , 90, 182102 | 3.4 | 9 |
| 94 | Wigner Rotation of Spin 1/2 Particles in Rindler Spacetime. <i>Journal of the Korean Physical Society</i> , 2007 , 50, 6-9 | 0.6 | 2 |
| 93 | Modeling of Semiconductor Nanowire Field-Effect Transistors Considering Schottky-Barrier-Height Lowering. <i>Journal of the Korean Physical Society</i> , 2007 , 51, 298 | 0.6 | 3 |
| 92 | Equivalent circuit model of semiconductor nanowire diode by SPICE. <i>Journal of Nanoscience and Nanotechnology</i> , 2007 , 7, 4089-93 | 1.3 | |
| 91 | Fabrication of poly-silicon nano-wire transistors on plastic substrates. <i>Journal of Nanoscience and Nanotechnology</i> , 2007 , 7, 4150-3 | 1.3 | |

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|----|--|-----|----|
| 90 | DC Transport Characteristics of Lambda DNA Molecules and Effect of RF Signals. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 5471-5473 | 1.4 | |
| 89 | Final state boundary condition of the Schwarzschild black hole. <i>Physical Review D</i> , 2006 , 74, | 4.9 | 31 |
| 88 | Optical gain and luminescence of a ZnO-MgZnO quantum well. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 349-351 | 2.2 | 11 |
| 87 | Gate bias controlled NDR in an in-plane-gate quantum dot transistor. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006 , 32, 532-535 | 3 | 4 |
| 86 | Spontaneous and piezoelectric polarization effects in wurtzite ZnO/MgZnO quantum well lasers. <i>Applied Physics Letters</i> , 2005 , 87, 253509 | 3.4 | 91 |
| 85 | Non-Markovian gain and luminescence of an InGaN-AlInGaN quantum-well with many-body effects. <i>IEEE Journal of Quantum Electronics</i> , 2005 , 41, 1253-1259 | 2 | 4 |
| 84 | Non-Markovian decoherence: complete positivity and decomposition. <i>Journal of Modern Optics</i> , 2005 , 52, 935-943 | 1.1 | 7 |
| 83 | Intervalley interactions in Si quantum dots. <i>Journal of Applied Physics</i> , 2005 , 98, 033709 | 2.5 | 14 |
| 82 | A wide dynamic range analog predistortion-type linearizer using self-cancellation scheme. <i>IEEE Microwave and Wireless Components Letters</i> , 2005 , 15, 661-663 | 2.6 | 5 |
| 81 | Entanglement generates entanglement: entanglement transfer by interaction. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2005 , 338, 192-196 | 2.3 | 7 |
| 80 | Optical Gain in Wurtzite ZnO/ZnMgO Quantum Well Lasers. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, L1403-L1406 | 1.4 | 3 |
| 79 | Electrical Transport Properties of Au-Doped Deoxyribonucleic Acid Molecules. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 2623-2625 | 1.4 | 8 |
| 78 | Optical Gain in GaN Quantum Well Lasers with Quaternary AlInGaN Barriers. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 7460-7463 | 1.4 | 12 |
| 77 | Formation of Electrical Interconnects by Self-Trapping of Deoxyribonucleic Acid Molecules. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 3803-3805 | 1.4 | 4 |
| 76 | Generation of Local Magnetic Field by Nano Electro-Magnets. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 2054-2056 | 1.4 | 10 |
| 75 | Microwave design and characterization of a cryogenic dip probe for time-domain measurements of nanodevices. <i>Review of Scientific Instruments</i> , 2004 , 75, 2455-2460 | 1.7 | 8 |
| 74 | Effect of Ti thickness on contact resistance between GaN nanowires and Ti/Au electrodes. <i>Applied Physics Letters</i> , 2004 , 85, 1636-1638 | 3.4 | 22 |
| 73 | Fabrication and characterization of metal-semiconductor field-effect-transistor-type quantum devices. <i>Journal of Applied Physics</i> , 2004 , 96, 704-708 | 2.5 | 4 |

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|----|---|-----|----|
| 72 | Exciton Binding Energies in Zincblende GaN/AlGaN Quantum Wells. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 140-143 | 1.4 | 6 |
| 71 | Transport measurements through stacked InAs self-assembled quantum dots in time domain. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 460-463 | 3 | 3 |
| 70 | Finite element analysis of valence band structures in quantum wires. <i>Journal of Applied Physics</i> , 2004 , 96, 2055-2062 | 2.5 | 20 |
| 69 | Electronic Properties of InGaAs/GaAs Strained Coupled Quantum Dots Modeled by Eight-Band k \cdot p Theory. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 144-149 | 1.4 | 6 |
| 68 | Single-electron tunneling in silicon-on-insulator nano-wire transistors. <i>Superlattices and Microstructures</i> , 2003 , 34, 245-251 | 2.8 | 1 |
| 67 | Electrical conduction measurement of thiol modified DNA molecules. <i>Superlattices and Microstructures</i> , 2003 , 34, 433-438 | 2.8 | 17 |
| 66 | Transport study of ultra-thin SOI MOSFETs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 19, 39-43 | 3 | 3 |
| 65 | Relativistic entanglement and Bell's inequality. <i>Physical Review A</i> , 2003 , 67, | 2.6 | 90 |
| 64 | Magnetotransport measurements through stacked InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2003 , 82, 1230-1232 | 3.4 | 7 |
| 63 | Silicon single-electron transistors with sidewall depletion gates and their application to dynamic single-electron transistor logic. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 627-635 | 2.9 | 31 |
| 62 | Double-dot-like charge transport through a small size silicon single electron transistor. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 13, 946-949 | 3 | 9 |
| 61 | Direct observation of excited states in double quantum dot silicon single electron transistor. <i>Microelectronic Engineering</i> , 2002 , 63, 129-133 | 2.5 | 2 |
| 60 | Dense coding in entangled states. <i>Physical Review A</i> , 2002 , 66, | 2.6 | 57 |
| 59 | An automated glitch-detection/restoration method of atomic force microscope images. <i>Review of Scientific Instruments</i> , 2002 , 73, 3245-3250 | 1.7 | 2 |
| 58 | Single-Electron Transistors with Sidewall Depletion Gates on a Silicon-On-Insulator Nano-Wire. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 2574-2577 | 1.4 | 3 |
| 57 | Spontaneous Polarization and Piezoelectric Effects on Inter-Subband Scattering Rate in Wurtzite GaN/AlGaIn Quantum-Well. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L941-L944 | 1.4 | 10 |
| 56 | Single-electron transistor based on a silicon-on-insulator quantum wire fabricated by a side-wall patterning method. <i>Applied Physics Letters</i> , 2001 , 79, 3812-3814 | 3.4 | 26 |
| 55 | Selective growth of InAs self-assembled quantum dots on nanopatterned SiO ₂ /Si substrate. <i>Applied Physics Letters</i> , 2001 , 78, 1403-1405 | 3.4 | 20 |

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|----|---|-----|-----|
| 54 | Fabrication of quantum dot transistors incorporating a single self-assembled quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 430-434 | 3 | 5 |
| 53 | Spontaneous polarization and piezoelectric effects on intraband relaxation time in a wurtzite GaN/AlGaIn quantum well. <i>Applied Physics A: Materials Science and Processing</i> , 2000 , 71, 589-592 | 2.6 | 3 |
| 52 | Screening Effects on Electron-Longitudinal Optical-Phonon Intersubband Scattering in Wide Quantum Well and Comparison with Experiment. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 6601-6605 | 1.4 | 9 |
| 51 | Application of atomic-force-microscope direct patterning to selective positioning of InAs quantum dots on GaAs. <i>Applied Physics Letters</i> , 2000 , 77, 2607-2609 | 3.4 | 42 |
| 50 | Intraband relaxation time effects on non-Markovian gain with many-body effects and comparison with experiment. <i>Semiconductor Science and Technology</i> , 2000 , 15, 203-208 | 1.8 | 105 |
| 49 | Nano-Structure Fabrication and Manipulation by the Cantilever Oscillation of an Atomic Force Microscope. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 7257-7259 | 1.4 | 9 |
| 48 | Piezoelectric effects on many-body optical gain of zinc-blende and wurtzite GaN/AlGaIn quantum-well lasers. <i>Applied Physics Letters</i> , 1999 , 75, 1354-1356 | 3.4 | 20 |
| 47 | Fabrication and electrical characterization of planar resonant tunneling devices incorporating InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 1999 , 75, 1167-1169 | 3.4 | 20 |
| 46 | Intraband Relaxation Time in Wurtzite GaN/InAlN Quantum-Well. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L815-L818 | 1.4 | 5 |
| 45 | Macromodeling of single-electron transistors for efficient circuit simulation. <i>IEEE Transactions on Electron Devices</i> , 1999 , 46, 1667-1671 | 2.9 | 51 |
| 44 | Non-Markovian gain of strained-layer wurtzite GaN quantum-well lasers with many-body effects. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1998 , 4, 520-526 | 3.8 | 4 |
| 43 | Theory of non-Markovian gain in strained-layer quantum-well lasers with many-body effects. <i>IEEE Journal of Quantum Electronics</i> , 1998 , 34, 344-352 | 2 | 24 |
| 42 | Many-body effects on optical gain in strained hexagonal and cubic GaN/AlGaIn quantum well lasers. <i>Applied Physics Letters</i> , 1997 , 71, 398-400 | 3.4 | 20 |
| 41 | Theory of non-Markovian optical gain in quantum-well lasers. <i>Progress in Quantum Electronics</i> , 1997 , 21, 249-287 | 9.1 | 120 |
| 40 | Optical gain of strained hexagonal and cubic GaN quantum-well lasers. <i>Applied Physics Letters</i> , 1996 , 69, 3303-3305 | 3.4 | 11 |
| 39 | Band-structure engineering of a cubic GaN quantum-well laser. <i>IEEE Photonics Technology Letters</i> , 1996 , 8, 194-196 | 2.2 | 8 |
| 38 | Optical gain of a quantum-well laser with non-Markovian relaxation and many-body effects. <i>IEEE Journal of Quantum Electronics</i> , 1996 , 32, 960-965 | 2 | 31 |
| 37 | Non-Markovian gain of a quantum-well laser with many-body effects. <i>Applied Physics Letters</i> , 1996 , 69, 2498-2500 | 3.4 | 7 |

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|----|--|-----|----|
| 36 | Screening effects on the band-gap renormalization of strained InGaAs/InGaAsP quantum well lasers lattice matched to GaAs. <i>Applied Physics Letters</i> , 1996 , 68, 1844-1846 | 3.4 | 9 |
| 35 | Optical gain of InGaP and cubic GaN quantum-well lasers with very strong spin-orbit coupling. <i>Journal of Applied Physics</i> , 1996 , 79, 7731-7737 | 2.5 | 14 |
| 34 | Calculations of hole-phonon scattering in strained-layer quantum wells. <i>Journal of Applied Physics</i> , 1995 , 78, 4505-4509 | 2.5 | 2 |
| 33 | Time-convolutionless reduced-density-operator theory of an arbitrary driven system coupled to a stochastic reservoir. II. Optical gain and line-shape function of a driven semiconductor. <i>Physical Review B</i> , 1995 , 51, 2159-2166 | 3.3 | 26 |
| 32 | Theoretical study of strained InGaP quantum-well lasers. <i>Applied Physics Letters</i> , 1995 , 66, 628-630 | 3.4 | 4 |
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